The enhancement of ferromagnetism in uniaxially stressed diluted magnetic semiconductors

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We predict a new mechanism of enhancement of ferromagnetic phase transition temperature T_c in uniaxially stressed diluted magnetic semiconductors (DMS) of p-type. Our prediction is based on comparative studies of both Heisenberg (inherent to undistorted DMS with cubic lattice) and Ising (which can be applied to strongly enough stressed DMS) models in a random field approximation permitting to take into account the spatial inhomogeneity of spin-spin interaction. Our calculations of phase diagrams show that area of parameters for existence of DMS-ferromagnetism in Ising model is much larger than that in Heisenberg model.

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I. INTRODUCTION

Recently (see[1,2] and references therein), great advances have been made in the problem of ferromagnetism (FMm) of p-doped diluted magnetic semiconductors (DMS). The question about influence of different physical phenomena in DMS on the critical temperature T_c of ferromagnetic (FM) phase transition is of prime interest for searching for the future study trends. After Pashitskii and Ryabchenko prediction of FMm in DMS,[3] the competition between FM correlations mediated by indirect long-range spin-spin interaction and direct short-range antiferromagnetic (AFM) interaction is considered to be decisive in the formation of FM state in DMS. In other words, to obtain FM state with high enough T_c, we need to inhibit the AFM contribution.

Due to short-range character of AFM interaction, only close pairs of magnetic ions contribute to it. This contribution can be minimized by decreasing the magnetic ion concentration n_i. On the other hand, when n_i is too small, ferromagnetism can be destroyed. To retain FM ordering in this case, we may increase the carriers concentration n_c (in p-type DMS this corresponds to holes concentration n_h). The calculations of T_c performed in a mean field approximation (MFA)[3] support this standpoint predicting an increase of T_c as $n_c^{1=3} n_i$.

However, at large n_c, the Friedel oscillations of carrier spin polarization become significant so that MFA becomes inapplicable. More thorough calculations with respect to Friedel oscillations (i.e. beyond MFA) corroborate above statement and show that in DMS undergoing FM phase transition n_c cannot exceed some critical value related to n_i. The reason for that is the oscillations of the RKKY interaction at the scale of $1=k_F \quad n_c^{1=3}$, which makes impossible long-range FM correlations if $\bar{r}k_F \quad 1$, ($\bar{r}$ is an inter-ion mean distance)[4].

To properly account for above Friedel oscillations, which is indeed a spatial dispersion of inter-ion interaction, we developed so-called random field approximation (RFA) in Ref.4. In that work, the ion-ion interaction has been considered in the context of Ising model. This model can be applied for axially symmetric semiconductors with magnetic ions interacting indirectly via holes (i.e. with RKKY interaction). The reason for Ising model usage for RKKY interaction is a complex structure of valence band in DMS that picks out the hole angular momenta projections $J_Z = \quad 3=2$ for lowest heavy hole subbands in crystals with distorted cubic or uniaxial lattice.

Additionally to spatial dispersion of inter-ion interaction, there are fluctuations of local magnetic field direction that also cannot be described in terms of MFA. This effect stems from the contribution of transversal spin components in effective Heisenberg - like Hamiltonian of spin-spin interaction. Namely, RKKY-interaction in p-doped undistorted DMS with cubic lattice represents this situation.

In the present paper we pay attention to the fact, that transition from Heisenberg spin-spin interaction to Ising one, i.e. exclusion of transversal spin components from Heisenberg Hamiltonian decreases the system entropy and therefore can enhance T_c. For quantitative description of this effect we present a comparative analysis of the RFA-theories for critical temperature T_c in Heisenberg and Ising models. This analysis has been made to determine the role of directional fluctuations (inherent to Heisenberg model) of localized spins in a random magnetic field. The uniaxial stresses in typical DMS-structures grown on a substrate with some mismatch of lattice constants is shown to be the factor responsible for appearance of Ising-like interaction between magnetic ions spins. Thus, we predict a new effect implying that increasing of T_c can be controlled within certain bounds by the uniaxial stresses in DMS. In other words, we expect that strain engineering can efficiently control the value of ferromagnetic phase transition temperature resulting from the hole-mediated exchange interaction between magnetic ions in DMS.

II. THEORETICAL BACKGROUND

A. Heisenberg model

The Hamiltonian of Heisenberg model for DMS reads

$$H = \sum_{j<j'} J(\vec{r}_{j;j'}) \vec{S}_j \vec{S}_{j'} + \sum_j \vec{H}_0 \vec{S}_j; \qquad (1)$$

where external magnetic field $\vec{H}_0$ and interaction $J(\vec{r}_{j;j'})$ is measured in energy units (i.e. $g = 1$, is the Bohr magneton). The transition to Ising model means, hereafter, keeping only $S_{jZ} S_{j'Z}$ -components in scalar product $\vec{S}_j \vec{S}_{j'}$.

The Hamiltonian (1) incorporates two kinds of randomness. First, (the spatial disorder) is that spin can be randomly present or absent in the specific j-th cite of a host semiconductor. Second, (the thermal disorder) is a random quantum state of a spin in j-th cite. These spatial and thermal fluctuations can be taken into consideration by introduction of random field rather than mean field.

In the random field approximation, we consider every spin $\vec{S}_j$ as a source of fluctuating (random) field

$$\vec{H}_{ri;j} = J(\vec{r}_i - \vec{r}_j)\vec{S}_j \qquad (2)$$

affecting other spin at the sites $\vec{r}_i$. In other words, every spin is subjected to some random (rather then mean) field, created by all other spins. So, all thermodynamic properties of the system will be determined by the distribution function $f(\vec{H}_r)$ of the random field $\vec{H}_r$. Namely, any spin dependent macroscopic quantity (like magnetization) $<< A >>$ reads

$$<< A >> = \int < A >_{\vec{H}_r} f(\vec{H}_r) d\vec{H}_r; \qquad (3)$$

where

$$< A >_{\vec{H}_r} = \frac{Tr\{A \exp(-H_Z/T)\}}{Tr\exp(-H_Z/T)} \qquad (4)$$

is a single particle thermal average with temperature T and effective Zeeman Hamiltonian $H_Z = \vec{H}_r \vec{S}$.

The distribution function $f(\vec{H}_r)$ is defined as

$$f(\vec{H}_r) = \left\langle \delta\left(\vec{H}_r + \sum_{j(\neq i)} J(\vec{r}_i - \vec{r}_j)\vec{S}_j - \vec{H}_0\right) \right\rangle; \qquad (5)$$

where the bar means averaging over spatial disorder. Our RFA approach is based on micro-canonical statistical theory of magnetic resonance line shape.[5] Latter theory assumes the additivity of local molecular field contributions $\vec{H}_r = \sum_j \vec{H}_{ri;j}$ of each particle j (Eq. (2)) as well as the non-correlative spatial distributions of magnetic ions.

Latter assumptions with respect to spectral representation of function permit to transform Eq. (5) to the non-linear integral equation for $f(\vec{H}_r)$ $f(\vec{H})$ in thermodynamic limit. Introducing the probability $n_i(\vec{r})d^3r$ for small volume d^3r to be occupied by a particle, we obtain

$$f(\vec{H}) = \int \exp\left[i\vec{\sigma}(\vec{H} - \vec{H}_0)\right] G(\vec{\sigma}) \frac{d^3\sigma}{(2)^3}; \qquad (6a)$$

$$G(\vec{\sigma}) = \int_V (\vec{r}) n_i(\vec{r}) d^3r; \qquad (6b)$$

$$(\vec{r}) \quad << 1 - \exp[iJ(\vec{r})\vec{S}\vec{\sigma}] >> =$$

$$= \int W(\vec{H}) f(\vec{H}) d^3H; \qquad (6c)$$

$$W(\vec{H}) = << 1 - \exp[iJ(\vec{r})\vec{S}\vec{\sigma}] >>_{\vec{H}}: \qquad (6d)$$

Eqs (6) represent the integral equation for distribution function $f(\vec{H})$. In general case this equation can be solved only numerically.

However, in many cases (e.g. for T_c or magnetization calculations) it is possible to avoid the solution of the integral equation since in these cases it is exactly reducible to the set of transcendental equations for macroscopic quantities like $<< S^n >>$, $1 \quad n \quad 2S$ of the system. Simplest situation corresponds to the case $S = 1/2$, where only magnetization $\vec{M} = g << \vec{S} >>$ (or in dimensionless units $\vec{m} = 2 << \vec{S} >>$; g is g-factor of a magnetic ion) is a unique order parameter to be found.

Thus, in the case of $H_0 = 0$ and $S = \frac{1}{2}\vec{\sigma}$ ($\vec{\sigma}$ are the Pauli matrices) Eq. (6a) takes the form

$$f(\vec{H}) = \int \exp\left[i\vec{\sigma}\vec{H}\right] \exp\left[-F_0\left(\frac{\vec{\sigma}}{2}\right) - i\vec{m}\vec{F}_1\left(\frac{\vec{\sigma}}{2}\right)\right] \frac{d^3\sigma}{(2)^3}; \qquad (7)$$

where

$$\vec{m} = \int \frac{\vec{H}}{H} \tanh\frac{H}{2T} f(\vec{H}) d^3H; \qquad (8)$$

$$F_0(x) = \int_V n(\vec{r})[1 - \cos(J(\vec{r})x)] d^3r; \qquad (9)$$

$$F_1(x) = \int_V n(\vec{r}) \sin(J(\vec{r})x) d^3r: \qquad (10)$$

Here $= |\vec{\sigma}| \sqrt{{}^2_x + {}^2_y + {}^2_z}$. To derive (7) we have used following property of Pauli matrices:

$$\exp(\vec{\sigma}\vec{b}) = \cosh b + \frac{\vec{\sigma}\vec{b}}{b}\sinh b; \quad b \quad |\vec{b}|: \qquad (11)$$

Substitution of equation (7) into Eq.(8) results in a single closed equation for order parameter $\vec{m}$:

$$\vec{m} = \frac{1}{(2\pi)^3}\int d^3\vec{H}\int d^3\vec{\sigma}\,\frac{\vec{H}}{H}\tanh\frac{H}{2T}\exp\left\{F_0\left(\frac{\vec{\sigma}}{2}\right) + i\vec{\sigma}\vec{B}\right\}; \qquad (12)$$

where

$$\vec{B} = \vec{H} - \vec{m}\frac{F_1\left(\frac{\vec{\sigma}}{2}\right)}{\vec{\sigma}}. \qquad (13)$$

To simplify the vector equation (12), we scalarwise multiply its left- and right-hand sides by $\vec{m}$ and integrate the resulting equation for scalar quantity $m\,|\vec{m}|$ over the angle between vectors $\vec{H}$ and $\vec{m}$. The final result (see Appendix A for details of its derivation) reads

$$m = 6\int_0^1 B^H_{1=2}(t)e^{F_0(t=2T)} R_2\left(mF_1\left(\frac{t}{2T}\right)\right)dt; \qquad (14)$$

$$B^H_{1=2}(t) = \frac{1}{3}\operatorname{csch} t(1 + t\coth t); \qquad (15)$$

$$R_n(x) = \frac{x\cos x - n\sin x}{x^n}. \qquad (16)$$

Trivial solution $m = 0$ of the equation (14) corresponds to paramagnetic phase. Under certain system parameters and temperatures, the equation (14) has nontrivial solution that determines the phase transition to the state with spontaneous magnetization.

To find the critical temperature T_c, we use the Landau theory with m as an order parameter. For this purpose, we may derive (see Appendix B for details of derivation) the free energy of the system in the form

$$F^H = F_0 + \frac{1}{2}m^2 + 6\int_0^1 B^H_{1=2}(t)e^{F_0(t=2T)}\frac{\sin\left(mF_1\left(\frac{t}{2T}\right)\right) - mF_1\left(\frac{t}{2T}\right)}{mF_1^2\left(\frac{t}{2T}\right)}dt. \qquad (17)$$

In the vicinity of T_c, the free energy (17) can be substituted by a Landau expansion

$$F^H_L = F_0 + \frac{1}{2}m^2\left(1 - 2A^H_1\right) + \frac{1}{20}m^4A^H_3; \qquad (18)$$

$$A^H_n = \int_0^1 B^H_{1=2}(t)e^{F_0(t=2T)}F_1^n\left(\frac{t}{2T}\right)dt;$$

where F_0 is a system free energy in a paramagnetic phase.

It should be noted here that contrary to conventional phenomenological Landau expansions of a free energy, the coefficients A^H_n in the function (18) have been derived microscopically within our RFA approach. Free energy functions (17) and (18) give a possibility to describe the experimentally observable equilibrium thermodynamic characteristics (like magnetic susceptibility, specific heat etc) of the DMS both in paramagnetic and in ferromagnetic phases.

According to Landau theory of phase transitions, the phase transition temperature T_c is reached, when coefficient $1 - 2A^H_1 = 0$ in Eq. (18). This is because T_c is defined as a temperature, where nonzero infinitesimal magnetization appears. Obviously, the same equation can be obtained from the Eq. (14) for magnetization in the limit $m \to 0$. The explicit form of the equation for $T_c \equiv T^H_c$ reads

$$1 = 2\int_0^1 B^H_S(t)F_1\left(\frac{t}{2T^H_c}\right)e^{F_0(t=2T^H_c)}dt; \qquad (19)$$

where $S = 1=2$ in our case.

Actually, the Eq. (19) determines the T^H_c as an implicit function of system parameters (like n_i, n_c etc). This function can be considered as a phase diagram that separates the region of parameters where the ferromagnetic phase with $m \neq 0$ exists from that where $m = 0$. Latter phase may be paramagnetic or spin glass phase. In principle, our RFA method permits to investigate this question. This study, however, is beyond the scope of the present paper.

The limit $T^H_c \to 0$ in (19) gives the relation between parameters of the system, which determines the condition for ferromagnetic ordering to occur in DMS at $T = 0$. The explicit form of this condition reads

$$1 < \frac{4}{3}\int_0^1 \frac{F_1(x)}{x}e^{F_0(x)}dx. \qquad (20)$$

B. Ising model

Let us consider now Ising model. In this case all effective magnetic fields are directed along OZ axis, so that scalar product reduces to $\vec{S}\vec{\sigma} = S_Z\sigma_Z$, $S_Z = -1=2; 1=2$ and Eq.(6a) becomes

$$f(H) = \frac{1}{2\pi}\int_{-1}^{1} e^{iH\sigma}G(\sigma)\,d\sigma; \qquad (21)$$

$$G(\sigma) = \prod_V\left(1 - n_i(\vec{r})\right)e^{i\sigma J(\vec{r})S_Z}d^3\vec{r} = \left(1 - n_i(\vec{r})\right)e^{-i\sigma J(\vec{r})/2}d^3\vec{r} =$$

$$= F_0\left(\frac{\sigma}{2}\right) + imF_1\left(\frac{\sigma}{2}\right); \qquad (22)$$

where definition of m is similar to Eq.(8):

$$m = \int_{-1}^{1}\tanh\left(\frac{H}{2T}\right)f(H)dH. \qquad (23)$$

Multiplying Eq.(21) by $\tanh(H=2T)$ and integrating over H, we obtain the transcendental equation for order pa-

rameter m . The explicit form of this equation reads

$$m = \int_{-1}^{1} B^{I}_{1=2}(t) \exp\left(F_0\left(\frac{t}{2T}\right)\right) \sin\left(m F_1\left(\frac{t}{2T}\right)\right) dt; \quad (24a)$$

where

$$B^{I}_{1=2}(x) = \frac{1}{2}\int_{-1}^{1} \tanh\left(\frac{h}{2}\right) \sin(xh)\, dh = \frac{1}{\sinh x}: \quad (24b)$$

The equations for free energy and critical temperature T_c can be obtained similarly to those for Heisenberg model. They read

$$F^{I} = F_0 + \frac{1}{2}m^2 \int_{-1}^{1} B^{I}_{1=2}(t) \exp\left(F_0\left(\frac{t}{2T}\right)\right) \frac{1 - \cos\left(m F_1\left(\frac{t}{2T}\right)\right)}{F_1\left(\frac{t}{2T}\right)} dt;$$

$$F^{I}_{L} = F_0 + \frac{1}{2}m^2\left(1 - A^{I}_{1}\right) + \frac{1}{24}m^4 A^{I}_{3};$$

$$A^{I}_{n} = 2\int_{0}^{1} B^{I}_{1=2}(t) \exp\left(F_0\left(\frac{t}{2T}\right)\right) F^{n}_{1}\left(\frac{t}{2T}\right):$$

Similar to Eq. (19), the explicit form of equation for T_c T^{I}_{c} reads

$$1 = 2\int_{0}^{1} B^{I}_{1=2}(t) F_1\left(\frac{t}{2T^{I}_{c}}\right) \exp\left(F_0\left(\frac{t}{2T^{I}_{c}}\right)\right) dt; \quad (25)$$

while the equation for FM m region in the phase diagram at $T = 0$ has following form

$$1 < \frac{2}{\pi}\int_{0}^{1} F_1(x) e^{F_0(x)} \frac{dx}{x}: \quad (26)$$

III. DISCUSSION OF RKKY INTERACTION

A. Non Gaussian fluctuations for S = 1=2

Let us analyze the equations for critical temperatures for Heisenberg (19) and Ising (25) models in more details. The difference between them consists only in the form of kernels of integrals for Heisenberg (Eq. (15)) and Ising (Eq. (24b)) cases, so that equation for critical temperature in Heisenberg model can be transformed to that in Ising model (and vice versa) by replacement of $B^{H}_{1=2}(t)$ with $B^{I}_{1=2}(t)$.

We start the analysis of these equations from their MFA asymptotics. To get this asymptotics, the functions $F_0(\ )$ and $F_1(\ )$ in the Eqs (9), (10) should be expanded up to linear terms: $F_0(\ ) \to 0, F_1(\ ) \to \bar{J}$, where $\bar{J} = \int_V n_i(r) J(r) d^3r$. After some algebra, the latter approximation allows to reduce the Eqs(19), (25) to the expressions for critical temperatures in Heisenberg T^{MF}_{M} (M = H) or Ising (M = I) models:

$$T^{MF}_{M} = 2\bar{J}\int_{0}^{1} B^{M}_{1=2}(t) t\, dt = \frac{1}{4}\bar{J}; \quad (27)$$

One can see that latter expression is identically the same to well-known MFA result for S = 1=2

$$T^{MF}_{c} = \frac{1}{3}S(S+1)\int_{V} n_i(r) J(r) d^3r: \quad (28)$$

The Eqs (27), (28) demonstrate also that MFA is independent of the choice of Heisenberg or Ising model, $T^{MF}_{H} = T^{MF}_{I} = T^{MF}_{c}$.

Next terms of expansion of the Eqs (9), (10) correspond to Gaussian asymptotics for distribution function of local fields. The purpose of subsequent analysis is to compare the (actual, i.e. non Gaussian) fluctuations of longitudinal components of random field with those of transversal ones.

Since our theory permits to find the distribution function f(H) when a spatial dependence of J(r) is assigned, we should specify a magnetic interaction in the system. Usually in the problems of carrier-induced ferromagnetism in DMS, the RKKY interaction[6] is considered as an effective spin-spin exchange interaction resulting in FM ordering. To clarify the role of transversal spin fluctuations, here we use the simplest possible form of the interaction and neglect all possible factors that can influence J(r) (such as nonparabolicity of carrier dispersion law etc, see Refs7,8,9,10,11 for more details). Also, the stresses may change the form of J(r); see below for discussion.

In the case of simple one band carrier structure, the RKKY interaction reads

$$J(r) = J_0 x_e^{4=3} R_4(2k_F r); \quad (29)$$

where $x_e = n_c/N_0$, $J_0 = \frac{3}{2\hbar^2}^{1=3} J^2_{ci}{}^{2=3} m_d$, J_{ci} is a carrier-ion exchange constant, $N_0 = 1/$ is a concentration of the cation cites, m_d is the density of states effective mass. Note that in our single band approximation, the effects of stress may influence on x_e and k_F; see[2] for details. The threshold temperature of ferromagnetic ordering in MFA now can be found by evaluation of integrals (28) with respect to (29):

$$T^{MF}_{c} = \frac{1}{24} J_0 x_i^{4=3} \quad {}^{1=3}: \quad (30)$$

Here, the factor $J_0 x_i^{4=3}$ is independent of carrier concentration, $x_i = n_i$ is a molar fraction of the magnetic ions. The ratio of electron and magnetic ion concentrations $= n_c/n_i = x_e/x_i$ plays a crucial role in our theory as a parameter separating the cases of relatively small fluctuations with $_c$ and that of large ones with $_c$; parameter $_c$ is indeed a dimensionless critical concentration (corresponding to equality sign in expressions (20) and (26) for Heisenberg and Ising models respectively).

The functions $F_0(x)$ and $F_1(x)$ in Eqs.(9), (10) (with respect to Eq.(29)) assume following form in the case of homogeneous magnetic ions distribution, $n_i(r) = n_i = const$,

$$F_{0;1}(\ ) = \int_1^{\infty} \varphi_{0;1}(\ )/6 \quad ;$$

$$\varphi_0(\ ) = \int_0^{1} f1 \quad \cos(\ R_4(y))g y^2 dy; \qquad (31)$$

$$\varphi_1(\ ) = \int_0^{} \sin(\ R_4(y))\, y^2 dy: \qquad (32)$$

In the case of spin $S = 1=2$, the result (30) of MFA can be recovered from Eqs (31), (32) by their expansion up to linear terms $\varphi_0(\ ) \to 0; \varphi_1(\ ) \to$ (of course, with their further substitution into Eq. (14) or Eq. (24a)). Gaussian asymptotics of distribution function corresponds to the next term of expansion of the Eq. (31), $\varphi_0(\ ) \to {}^2=30; \varphi_1(\ ) \to$.

To account for real (non-Gaussian) distribution of fluctuating local field, we do not expand Eqs (31),(32) and calculate them numerically.

In dimensionless variables, the equations for critical temperatures for both above models assume following form

$$\frac{1}{6}\int_{-1}^{1} B^M_{1=2}(t)\varphi_1\left(\frac{t}{2_M}\right) E_{1=2}\left(\frac{t}{M}\right) dt = 1;$$

$$E_{1=2}\left(\frac{t}{M}\right) = \exp\left(\frac{1}{6}\varphi_0\left(\frac{t}{2_M}\right)\right); \qquad (33)$$

where $_M = T_c^M/(J_0 x_e^{4=3})$; M stands for H (Heisenberg model) or I (Ising model). The result of calculation of T_c^M/T_c^{MF} with the help of Eq. (33) as a function of is reported in the Fig.1a. It is seen, that there are curves that separate the areas of system parameters (including temperature) where FM or non-FM phases occur.

Our results show the limited area of concentrations $0 < < _c$ which allow FM ordering in both considered models. So, we have found $_c = 0:2473$ for the Ising model and $0:0989$ for the Heisenberg model. Our results also show the critical character of dependence $T_c = T_c(\ )$ that can be well approximated by the function

$$T_c \simeq T_c^{MF}(1 \quad =_c) \ = \frac{J_0}{24} x_i^{4=3\ 1=3}(1 \quad =_c) \qquad (34)$$

with $\simeq 0:47$ and $\simeq 0:63$ for Heisenberg and Ising models respectively.

Thus, the fluctuations of transversal spin components suppress a tendency towards FM ordering in the range of concentration ratios $0 < < 0:099$. Moreover, in the range $0:099 < < 0:247$, our results predict impossibility of FM m in DMS with Heisenberg-like spin-spin interaction while in this interval of FM m can still occur in DMS with Ising- like interaction between spins. Since Ising model is inherent to uniaxially stressed semiconductors, latter conclusion means that uniaxial distortion can effectively inhibit transversal spin fluctuations thus enhancing T_c.

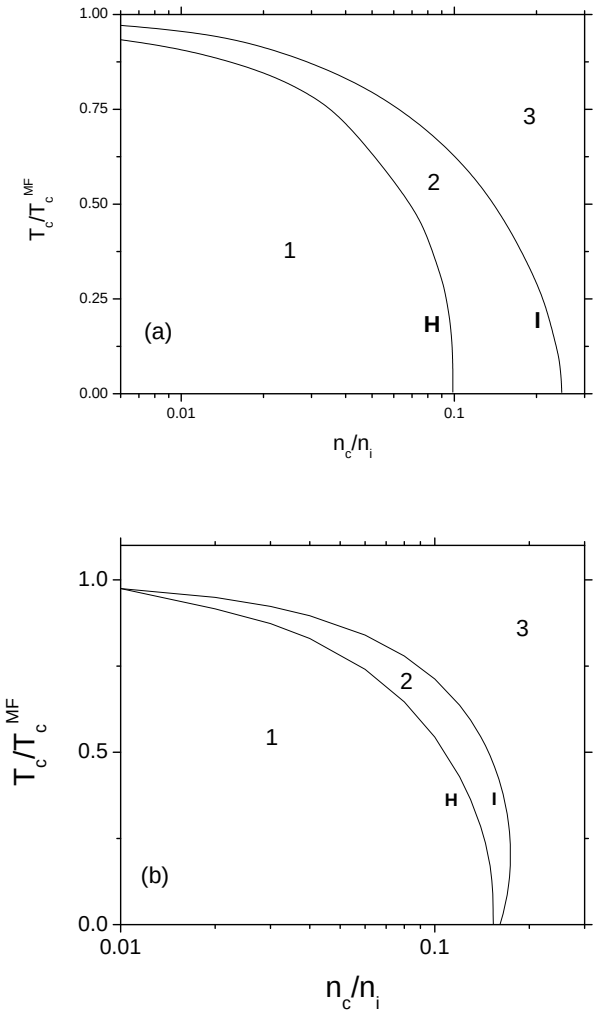

FIG. 1: The phase diagram of the systems under consideration. a) general (non-Gaussian) case for spin 1/2, b) Gaussian approximation for spin 5/2. H – Heisenberg model, I – Ising model. Region 1 corresponds to FM state for both models, region 2 corresponds to FM state for Ising model and non FM state for Heisenberg model, region 3 corresponds to non FM state for both models.

B. Gaussian fluctuations for S = 5=2

The equation (19) for critical temperature T_c is exact in the framework of our model, which means that it incorporates non-Gaussian fluctuations. At the same time it is restricted by the case of ion spins $S = 1=2$. Practically important case of Mn^{2+} ions with $S = 5=2$ needs a special consideration. Mathematically, the problems arise for $S > 1=2$, when exponential function of spin operator is no more a linear function so that Eq. (11) is no more valid. In this case we should use Sylvester theorem for exponent of a Hermitian matrix $(2S+1)$ $(2S+1)$ (see, e.g.[12] for more details). Appendix C presents the final result of such calculations for $W(H)$ and $S = 5=2$ (Eq.(6d)).

It is apparent from Appendix C that the case $S = 5/2$ involves much more order parameters (such as $a_{m,n} = \langle c^m{}_n \rangle = \int c^m{}_n f(\vec{H}) d^3H$, $m = 0;2;4$; $n = 0;1;2$, and $b_{m,n} = \langle c^m{}_n \rangle$, $m = 1;3;5$; $n = 0;1;2$) than in the case $S = 1/2$. Not all of them play a crucial role in formation of FM phase in DMS. For example, if the random field fluctuations are almost Gaussian, we can find the expectation values of spin operators (8) with the aid of only two parameters, representing first and second moments of the distribution function $f(H)$.

Our calculations show that Gaussian approximation for $f(H)$ adequately describes the actual phase diagram of DMS (except for close vicinity of critical concentration which is not practically important). That is why the analysis of the case of $S = 5/2$ can be performed with sufficient accuracy in Gaussian approximation. To do this, the Eq. (C6) should be substituted by its expansion in $t = J(\vec{r})$ up to the second order. The result reads

$$W(\vec{H}) = ic\left[3\coth\frac{3H}{T} - \frac{1}{2}\coth\frac{H}{2T}\right]J(\vec{r}) + \frac{5}{4}\left[1 + 4c^2\left(\frac{3c^2 - 1}{1 + 2\cosh\frac{2H}{T}}\right)\right]\frac{(J(\vec{r}))^2}{2}. \qquad (35)$$

We apply this result to obtain the equation for critical temperature. The magnetization and mean value of random field $\vec{H}$ are negligibly small at this temperature that suggests that $f(\vec{H})$ is isotropic. Thus, performing angular averaging over the directions of $\vec{H}$ in Eq.(6c), we can put $c^2 = 1/3$ in the Eq. (35).

To relate this result to the case $S = 1/2$, we note that first term of Eq. (35) includes Brillouin function for spin $S = 5/2$

$$B_S\left(\frac{SH}{T}\right) = \left(1 + \frac{1}{2S}\right)\coth\frac{(S + 1/2)H}{T} - \frac{1}{2S}\coth\frac{H}{2T}. \qquad (36)$$

After simple algebra, the Eq.(6c) takes following form for arbitrary spin S

$$\tilde{m}(\vec{r}) = i\tilde{m}SJ(\vec{r}) + \frac{1}{3}S(S + 1)\frac{(J(\vec{r}))^2}{2}; \qquad (37)$$

where

$$\tilde{m} = \int \frac{\vec{H}}{H} B_S\left(\frac{SH}{T}\right) f(\vec{H}) d^3H : \qquad (38)$$

One can see that the above equations are formally similar to those for $S = 1/2$ if we expand Eqs (9) and (10) up to first nonvanishing terms. The Eq. (37) determines the components of Fourier image of distribution function (7) in Gaussian approximation

$$F_0\left(\frac{}{2}\right) = \frac{1}{3}S(S + 1)\overline{J^2}\frac{}{2}; \quad F_1\left(\frac{}{2}\right) = S\overline{J}\,;$$
$$\overline{J^n} = \int_V n(\vec{r}) J^n(\vec{r}) d^3r. \qquad (39)$$

Equations (38) and (39) reduce the problem of T_c determination in Gaussian approximation for arbitrary ion spin to the case of non-Gaussian fluctuations for spin $S = 1/2$ considered above. Namely, after substitution of these equations to Eq. (19) along with proper generalization (for the case of arbitrary spin) of the function $B^H_{1/2}(t)$, we can use this equation to find T_c for any $S > 1/2$. Calculations performed in the same manner as Eqs. (A7) and (A8) yield

$$B^H_S(t) = \frac{1}{6S}\left[\coth\frac{t}{2S + 1} - \coth t + \frac{t}{6S}\left(\frac{\mathrm{csch}^2\frac{t}{2S+1}}{2S + 1} - \mathrm{csch}^2 t\right)\right]. \qquad (40)$$

It can be readily shown that in the case $S = 1/2$ the Eq. (40) reduces to simpler form (15).

Substitution of (39) to (20) permits to obtain the necessary condition for FM form formation at zeroth temperature in the form (see also Eqs. (20) and (26))

$$\overline{J} > \sqrt{\frac{3}{8}\frac{S + 1}{S}\overline{J^2}}. \qquad (41)$$

This inequality has clear physical meaning: small dispersion and positive (FM) inter-ion spin-spin interaction favors creation of FM form in DMS. Also, large spin is also preferable for FM form formation due to relatively small (quantum) fluctuations of its transversal components.

For comparison, we also consider Ising model for $S \geq 1/2$ in Gaussian approximation (despite the possibility to account for non-Gaussian fluctuations of ran-

dom eld for arbitrary S 1=2)[4]. Expansion of the function G( ) (Eq.(22)) with arbitrary S and m = $\int_{-1}^{1} B_S\left(\frac{SH}{T}\right) f(H)dH$ up to second order leads to the distribution function in the form (21) with G( ) in the form (22), where

$$F_0\left(\frac{}{2}\right) = M_2\overline{J^2}\frac{}{2}^2; \quad F_1\left(\frac{}{2}\right) = S\overline{J} : \qquad (42)$$

Parameters

$$m = \int_{-1}^{1} B_S\left(\frac{SH}{T}\right) f(H)dH \qquad (43)$$

and

$$M_2 = S_Z^2 = \int_{-1}^{1} Q_S\left(\frac{H}{T}\right) f(H)dH; \qquad (44)$$

$$Q_S\left(\frac{H}{T}\right) = S(S+1)$$

$$S\coth\left(\frac{H}{2T}\right) B_S\left(\frac{SH}{T}\right); \qquad (45)$$

should be found self-consistently with respect to Eqs. (21), (22) and (42). Thus, in Gaussian approximation, Ising model needs self-consistent determination of two parameters, $\langle\langle S_Z\rangle\rangle$ and S_Z^2 , while in the case of Heisenberg model single parameter $<<\hat{S}\hat{j}>>$ needs to be determined. This is because for Heisenberg-like interaction $<<S^2>> = S(S+1) = \text{const}$ (Eq. (39)) so that this parameter depend neither on temperature nor on eld distribution.

The critical temperature can be found from the Eqs (43) and (44) as m ! 0

$$1 = \frac{\overline{J}\sqrt{8}}{\sqrt{M_2\overline{J^2}}} \int_0^{1} xSB_S\left(\frac{\sqrt{3\ 2M_2\overline{J^2}}\,x}{S(S+1)\overline{J}}\right) e^{-x^2}dx; \qquad (46)$$

$$M_2 = \frac{2}{\sqrt{}} \int_0^{1} Q_S\left(\frac{\sqrt{3\ 2M_2\overline{J^2}}\,x}{S(S+1)\overline{J}}\right) e^{-x^2}dx; \qquad (47)$$

where = T_c/T_c^{MF} is a ratio of actual critical temperature and that obtained in MFA approximation (Eq. (28)). In this approximation, the necessary condition to form FM state at T = 0 in DMS has the form of following inequality

$$\overline{J} > \sqrt{\frac{}{2}\overline{J^2}}: \qquad (48)$$

The independence of Eq. (48) of spin can be thought of (see Eq. (41) for comparison) as a lack of transversal spin components contribution to random eld in Ising model.

Now we are ready to compare Heisenberg and Ising models for speci c case of RKKY interaction (29). In Gaussian approximation we have to evaluate only two integrals

$$\overline{J} = \frac{1}{6}J_0 x_i^{4=3\ 1=3}; \overline{J^2} = \frac{2^{\ 2}}{5}\ \overline{J}^{\ 2}: \qquad (49)$$

Note that the equations (49) demonstrate the relation between Friedel oscillations and rst (/ $\overline{J}$) and second (/ $\overline{J^2}$) moments of distribution function of random magnetic elds. Namely, at frequent Friedel oscillations (i.e. large n_c and) the in uence of dispersion $(\overline{J^2})^{1=2}$ (which is "responsible" for disorder in the system) prevail over trend to order the system due to mean value $\overline{J}$.[4] This means that frequent Friedel oscillations at the scale of mean inter-ion distance inhibit ferromagnetism in DMS.

Substitution of (49) into (46), (47) permits to nd the dependence ( ) for practically important case S = 5=2 (see Fig.1b). One can see that qualitatively situations for S = 5=2 and S = 1=2 are similar: the region of FM state is signi cantly larger for Ising model than that for Heisenberg model. But there is also a di erence. Comparison of Fig.1a and 1b shows that the area between curves $T_c(n_c=n_i)$ for Heisenberg (H) and Ising (I) models at low temperatures is smaller for S = 5=2. This means that for S = 5=2 quantum uctuations (which is the only possible uctuations at T = 0) are inhibited as compared to the case S = 1=2.

This is actually a re ection of the well known fact that the larger the magnitude of the quantum number of the spin, the "more classical" it is, i.e. the smaller is the contribution of quantum uctuations of its transversal components. At T 6 0 additional thermal uctuations appear. It is seen from the Figure, that at T T_c the extension of FM phase due to enhancement of T_c is almost the same for S = 5=2 and S = 1=2. This means that the thermal uctuations of the spin do not sensitive to its value.

IV. CONCLUSIONS

In this paper we have proposed a new mechanism of the enhancement of FM phase transition temperature T_c by the uniaxial distortion of DMS. This prediction is based on comparative analysis of Heisenberg (inherent to undistorted DMS) and Ising (inherent to uniaxially distorted DMS) models. The analysis of above models has been carried out in the framework of our recently developed formalism,[4] random eld method. This method, which can be regarded as a substitution of conventional MFA for disordered systems with given J(r), permits to derive self-consistently the equations for order parameter m and the free energy functions of DMS.

Now we discuss in more details the in uence of stresses on magnetic spin Hamiltonian of DMS (1). We consider such in uence in two steps. In rst step we consider the in uence of the stress on the e ective spin-spin interaction potential and in second step we consider the operator part of the Hamiltonian.

Since the effective potential of indirect spin-spin interaction strongly depends on the band structure of specific semiconductor sample, which is affected by the stress, this potential by itself may also depend on stress. This influence[2] is manifested via both density of states (in our case we use the effective mass of density of states m_d (29)) at the Fermi level and concentration of free holes, related to pinning of the Fermi level by defects and impurities of different nature. As it was noted in Ref.[7], the influence of pressure on the density of states is small. The influence via pinning centers depends entirely on their nature. We can imagine the situation when the influence of pressure on the concentration is also small. For example, in the cases of the absence (or small number) of pinning centers or "synchronous movement" of pinning centers with the valence band edge shift due to deformation potential, this effect is negligible and our mechanism of influence of the pressure will be decisive. Here we would like to emphasize that there are no general problems to incorporate the possible dependence of the concentration on the stress into our consideration (this is simply one more modification of $J(\vec{r}_{ij})$ in (1)). If we do so, the considered effect of elimination of transversal spin components by the stress, which has not been discussed in the literature, is an additional factor enhancing T_c:

To discuss the stress effect on the operator part, we note that in the typical case of p-type DMS with cubic lattice the transversal spin-spin interaction can be substantially inhibited by the uniaxial stress of a crystal. Really, such stress splits the valence band edge to light and heavy hole subbands. The resulting heavy hole (HH) states are characterized by angular momentum projection $J_Z = \pm 3/2$. For such states, the spin-flip scattering of these holes on magnetic ions is forbidden due to angular momentum conservation. Hence only longitudinal (along the distortion axis) Z-components of the spins will be present in the resulting indirect spin-spin interaction via above heavy holes.

However, aforementioned spin-flip processes are not forbidden both for light hole (LH) states (with spin projection $\pm 1/2$) and for transitions between LH and HH states thus contributing to the indirect interaction of transversal spin components of magnetic ions. Hence, the deformational splitting of a valence band edge, leading to preferential occupancy of the heavy hole subbands gives the anisotropy of indirect spin-spin interaction in the form $H = \sum_{i>j} J_{ki;j} S_{Z\,i} S_{Z\,j} + J_{?\,i;j} (S_{X\,i} S_{X\,j} + S_{Y\,i} S_{Y\,j})$. The ratio $= J_{?\,i;j}/J_{ki;j}$ $(0 < < 1)$ should be monotonically decreasing function of the ratio of heavy holes concentration n_{HH} to their complete concentration n_H. Thus, if deformational HH – LH splitting exceeds the Fermi energy of the holes, the ratio n_{HH}/n_H reaches its maximal value ($n_{HH}/n_H \to 1$), corresponding to Ising Hamiltonian ($\to 0$) of the indirect spin-spin interaction. In this case the region of ferromagnetic state of DMS expands substantially towards both higher carriers (holes) concentration and higher temperatures.

The detailed theoretical description of all above effects, which is intimately related to the parameters of specific DMS sample and experimental conditions, can be developed within the framework of presented theory for any particular case. However, such calculations can be done only numerically. Note, that the magnitude of effect which we predicted is very sensitive to the holes concentration n_h. The problem of its correct determination, to the best of our knowledge, is related to the influence of anomalous Hall effect. Latter effect lowers reliability of n_h determination from Hall effect data[13,14].

For better illustration of our effect, we estimate now the magnitude of T_c increase for typical ferromagnetic DMS $Ga_{1-x}Mn_xAs$ deposited on GaAs and GaP substrates. The mismatch a of lattice constant a leads to biaxial strain that splits the valence band with deformation potential $b = -1.7$ eV by the value $E_{1,2} = 2|b|\varepsilon^0_{zz}|$[15] where zz-component of strain tensor $\varepsilon^0_{zz} = 2(-a/a)c_{12}/c_{11}$, and the ratio of elastic moduli in GaAs $c_{12}/c_{11} = 0.453$. For $x = 0.035$ (or concentration $n_i = 7.76 \cdot 10^{20}$ cm^{-3}), the relative mismatch $|a/a| = 0.002$ for GaAs substrate and $|a/a| = 0.036$ for GaP substrate.[7] We can see that for GaAs substrate small valence band splitting $E_{1,2} \simeq 6$ meV cannot suppress interaction of transversal Mn-spin components for typical concentration $n_c = 10^{20}$ cm^{-3} which corresponds to Fermi energy $\varepsilon_F \simeq 80$ meV, whereas for GaP substrate $E_{1,2} \simeq 109$ meV $> \varepsilon_F$. Thus, our mechanism predicts the enhancement of T_c for $Ga_{1-x}Mn_xAs$ on GaP substrate by the factor 1.64 (see Fig.1b for $= n_c/n_i = 0.13$) as compared to the same DMS but on GaAs substrate.

Let us finally note that in the present paper we considered the enhancement of T_c due to RKKY interaction only. But there are also other mechanisms, which can lead to appearance of ferromagnetism in DMS, see[2] for details. These mechanisms will be eventually reduced to the Hamiltonian (1) with modified potential $J(\vec{r}_{ij})$. Thus for quantitative discussion of these mechanisms it is sufficient to substitute the corresponding modified potential to our self-consistent equations.

APPENDIX A

We begin with equation (12) for magnetization.

$$m = \frac{1}{(2\pi)^3} \int d^3H \int d^3\tilde{\omega} \frac{H}{H} \tanh\frac{H}{2T} \exp\left\{ F_0\left(\frac{1}{2}\right) + i\tilde{\omega}B \right\}; \qquad (A1)$$

First, we pass to spherical system for $\vec{\sim}$ and integrate the Eq.(A1) over $\vec{\sim}$ directions. This yields

$$\vec{m} = \frac{1}{2^{\ 2}} \int d^3\vec{H} \int_0^{\ 1} {}^2 d \ \frac{\vec{H}}{H} \tanh\frac{H}{2T} \exp\left[F_0 \ \frac{}{2} \ \right] \frac{\sin B}{B}; \tag{A2}$$

$$B = |\vec{B}| = \sqrt{H^2 \ \ 2\cos \ mHF_1(\ =2)= \ + (mF_1(\ =2)= \ )^2}; \tag{A3}$$

where is an angle between vectors $\vec{m}$ and $\vec{H}$.

Next step is a scalar multiplication of its both sides by $\vec{m}$ that yields

$$m^2 = \frac{1}{2^{\ 2}} \int d^3\vec{H} \int_0^{\ 1} {}^2 d \ \frac{\vec{H}\vec{m}}{H} \tanh\frac{H}{2T} \exp\left[F_0 \ \frac{}{2} \ \right] \frac{\sin B}{B}$$

or

$$m = \frac{1}{2^{\ 2}} \int d^3\vec{H} \int_0^{\ 1} {}^2 d \ \cos \ \tanh\frac{H}{2T} \exp\left[F_0 \ \frac{}{2} \ \right] \frac{\sin B}{B} \tag{A4}$$

The rotational invariance of scalar product permits to point $\vec{H}$ along z axis and integrate over angular variables in (A4). This yields

$$m = \frac{1}{2^{\ 2}} \int_0^{\ 2} d' \int_0^{\ } \sin \ d \int_0^{\ 1} H^2 dH \int_0^{\ 1} {}^2 d \ \cos \ \tanh\frac{H}{2T} \exp\left[F_0 \ \frac{}{2} \ \right] \frac{\sin B}{B};$$

where B is de ned by A3). Consider

$$I = \frac{1}{} \int_0^{\ 2} d' \int_0^{\ } \sin \ \cos \ \frac{\sin B}{B} d \ :$$

Change of variables

$$\cos \ = z = \frac{H^2 + (mF_1(\ =2)= \ )^2 \ \ B^2}{2mHF_1(\ =2)=}$$

with the help of (A3) reduces it to the form

$$I = \frac{}{(mHF_1(\ )= \ )^2} \int_{H \ mF_1(\ )=}^{H+mF_1(\ )=} \left[H^2 + (mF_1(\ =2)= \ )^2 \ \ B^2 \right] \sin B \ \ dB =$$

$$= \ 4 \ R_2(mF_1(\ =2))R_2(H \ ); \ R_n(x) = \frac{x\cos x \ \ \sin x}{x^n}: \tag{A5}$$

Substitution of (A5) into (A4) gives

$$m = \frac{2}{} \int_0^{\ 1} dH \int_0^{\ 1} d \ \tanh\frac{H}{2T} \exp\left[F_0 \ \frac{}{2} \ \right] R_2(mH_1(\ =2))R_0(H \ ): \tag{A6}$$

It is also possible to integrate over H in (A6)

$$\int_0^{\ 1} \tanh\frac{H}{2T} R_0(H \ ) \, dH = \ \ 3 \ TB^H_{1=2}(t); \ t = \ T: \tag{A7}$$

$$B^H_{1=2}(t) = \frac{\sinh \ t + \ t\cosh \ t}{3\sinh^2 \ t}: \tag{A8}$$

With respect to substitution $T = t$ this gives nal equation for m in the form (14) of the text.

APPENDIX B

We start the derivation of the free energy from the equation (14) for magnetization (order parameter). We rewrite it in the form

$$m + 6 \int_0^{\ 1} B^H_{1=2}(\ t)e^{\left[F_0(t=2T) \right]} R_2 \ \left[mF_1 \ \frac{t}{2T} \right] \ dt = 0: \tag{B1}$$

Now we recollect that if we have a free energy F of a system, then the equation for order parameter (in our

case Eq. (B1)) should minimize it. In other words, Eq. (B1) should be equivalent to condition

$$\frac{\partial F}{\partial m} = 0: \qquad (B2)$$

Condition (B2) is a simple differential equation for F, its solution yields

$$F = \int^{m} dm\ \left[m + 6 \int_0^{\infty} B^H_{1=2}(t) e^{F_0(t=2T)} R_2\left[m F_1\left[\frac{t}{2T}\right]\right] dt \right] =$$
$$= F_0 + \frac{1}{2}m^2 + 6 \int_0^{\infty} B^H_{1=2}(t) e^{F_0(t=2T)} \frac{\sin\left[m F_1\left[\frac{t}{2T}\right]\right]}{m F_1^2\left[\frac{t}{2T}\right]} dt: \qquad (B3)$$

This is indeed equation (17) from the text.

To get Landau expansion of (B3), we simply expand $\sin\left[m F_1\left[\frac{t}{2T}\right]\right]$ in Taylor series at small m. This gives

$$F = F_0 + 6 \int_0^{\infty} \frac{B^H_{1=2}(t) e^{F_0(t=2T)}}{F_1\left[\frac{t}{2T}\right]} dt + \frac{1}{2}m^2 \left[m^2 A^H_1 + \frac{1}{20} m^4 A^H_3 + \ldots \right]; \qquad (B4)$$
$$A^H_n = \int_0^{\infty} B^H_{1=2}(t) e_1^{F_0(t=2T)} F_1^n\left[\frac{t}{2T}\right] dt:$$

Paying attention that second term in (B4) does not depend on m and hence just renormalizes F_0, we easily obtain Eq. (18) from the text.

APPENDIX C

We are looking for the expression (6d) for the case $S = 5=2$. We introduce notation $\tilde{t} = J(r)\tilde{}$ and assume $T = 1$ (i.e. $\tilde{H}$ means $\tilde{H}=T$). In these notations Eq.(6d) reads

$$W(\tilde{H}) = 1 - \frac{\mathrm{Tr}\left\{ \exp\left[i\tilde{S}\tilde{t} \right] \exp\left[\tilde{S}\tilde{H} \right] \right\}}{\mathrm{Tr}\left\{ \exp\left[\tilde{S}\tilde{H} \right] \right\}}: \qquad (C1)$$

The denominator in Eq.(C1) can be immediately evaluated in a reference frame rotating around quantization axis

$$\mathrm{Tr}\left\{ \exp\left[\tilde{S}\tilde{H} \right] \right\} = \frac{\sinh 3H}{\sinh H=2}: \qquad (C2)$$

We introduce the functions

$$\gamma_n = \frac{\cosh(nH)}{1 + 2\cosh(2H)}; \qquad (C3)$$
$$\gamma_n = \frac{\cosh(nH)(\cosh H - 1)}{\sinh 3H} = \qquad (C4)$$
$$= \frac{\cosh(nH)\sinh H=2}{\cosh H=2 + \cosh 3H=2 + \cosh 5H=2}$$

and cosine of the angle between vectors $\tilde{H}$ and $\tilde{k}\tilde{t}$,

$$c = \cos\left[\hat{H}, \tilde{\kappa} \right] = \frac{\tilde{H}\tilde{\kappa}}{H}: \qquad (C5)$$

In these notations after lengthy calculations we can get the expression for the trace in numerator of Eq. (C1). With respect to Eq. (C2), this expression assumes the form

$$
\begin{aligned}
W(H) = {} & 1 - \frac{1}{4}\cos\frac{t}{2}\left[3 - (14\tilde{c}^2 + 15\tilde{c}^4)_0 - 4(1 - (6\tilde{c}^2 + 5\tilde{c}^4)_1 + 5(1 - \tilde{c}^2)_2\right] \\
& \frac{1}{8}\cos\frac{3t}{2}\left(1 + 3\tilde{c}^2 - 45\tilde{c}^4\right)_0 + 4(1 - (12\tilde{c}^2 + 15\tilde{c}^4)_1 + 5(1 + 2\tilde{c}^2 - 3\tilde{c}^4)_2 \\
& \frac{1}{8}\cos\frac{5t}{2}\left[3 - (10\tilde{c}^2 + 15\tilde{c}^4)_0 + 4(1 - 5\tilde{c}^4)_1 + (1 + 10\tilde{c}^2 + 5\tilde{c}^4)_2\right] + \\
& + \frac{ic}{4}\sin\frac{t}{2}\left[3 - (14\tilde{c}^2 + 15\tilde{c}^4)_0 - 4(1 - (6\tilde{c}^2 + 5\tilde{c}^4)_1 + 5(1 - \tilde{c}^2)_2\right] \\
& \frac{ic}{8}\sin\frac{3t}{2}\left[3 - (26\tilde{c}^2 + 15\tilde{c}^4)_0 - 4(3 - 4\tilde{c}^2 + 5\tilde{c}^4)_1 - 5(3 - 2\tilde{c}^2 - \tilde{c}^4)_2\right] + \\
& + \frac{ic}{8}\sin\frac{5t}{2}\left[15 - (10\tilde{c}^2 + 3\tilde{c}^4)_0 + 4(5 - \tilde{c}^4)_1 + (5 + 10\tilde{c}^2 + c^4)_2\right] : \qquad (C\,6)
\end{aligned}
$$

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